L Number	Hits	Search Text	DB	Time stamp
1	619395	chamber	USPAT; US-PGPUB	2004/03/30 18:46
2	64767	chamber and plasma	USPAT; US-PGPUB	2004/03/30 18:46
3	37239	(chamber and plasma) and current	USPAT; US-PGPUB	2004/03/30 18:47
4	8902	((chamber and plasma) and current) and bias	USPAT; US-PGPUB	2004/03/30 18:47
5	7281	(((chamber and plasma) and current) and bias) and volt$6	USPAT; US-PGPUB	2004/03/30 18:47
6	6601	((((chamber and plasma) and current) and bias) and volt$6) and (wafer substrate)	USPAT; US-PGPUB	2004/03/30 18:43
7	1	(((((chamber and plasma) and current) and bias) and volt$6) and (wafer substrate)) and ((control$6 monitor$3) with (ground near5 current) with (bias near5 volt$6))	USPAT; US-PGPUB	2004/03/30 18:45
8	13	(((((chamber and plasma) and current) and bias) and volt$6) and (wafer substrate)) and ((control$6 monitor$3) same (ground near5 current) same (bias near5 volt$6))	USPAT; US-PGPUB	2004/03/30 18:48
9	892495	chamber	EPO; JPO; DERWENT; IBM_TDB	2004/03/30 18:46
10	32826	chamber and plasma	EPO; JPO; DERWENT; IBM_TDB	2004/03/30 18:47
11	2890	(chamber and plasma) and current	EPO; JPO; DERWENT; IBM_TDB	2004/03/30 18:47
12	153	((chamber and plasma) and current) and bias	EPO; JPO; DERWENT; IBM_TDB	2004/03/30 18:47
13	101	(((chamber and plasma) and current) and bias) and volt$6	EPO; JPO; DERWENT; IBM_TDB	2004/03/30 18:48
14	2	((((chamber and plasma) and current) and bias) and volt$6) and ((control$6 monitor$3) same (ground near5 current) same (bias near5 volt$6))	EPO; JPO; DERWENT; IBM_TDB	2004/03/30 18:48